

### General Description

The WSF07N10 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF07N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	21	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	1.25	W
$T_{STG}$	Storage Temperature Range	-55 to 170	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 170	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	70	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.5	$^\circ C/W$

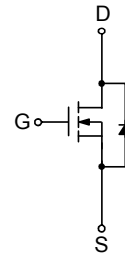
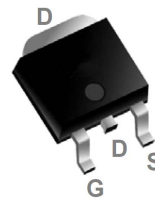
### Product Summary

BVDSS	RDSON	ID
100V	195m $\Omega$	7A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

### TO-252 Pin Configuration



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.098	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =1A	---	195	250	mΩ
		V <sub>GS</sub> =6V, I <sub>D</sub> =1A	---	240	320	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.5	2.0	3.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.57	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	---	1	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2	4	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.3A	---	5.2	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	0.75	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.4	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A, R <sub>L</sub> =30Ω	---	6	---	ns
T <sub>r</sub>	Rise Time		---	10	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	10	---	
T <sub>f</sub>	Fall Time		---	6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	---	320	---	pF
C <sub>oss</sub>	Output Capacitance		---	22	---	
C <sub>riss</sub>	Reverse Transfer Capacitance		---	13	---	

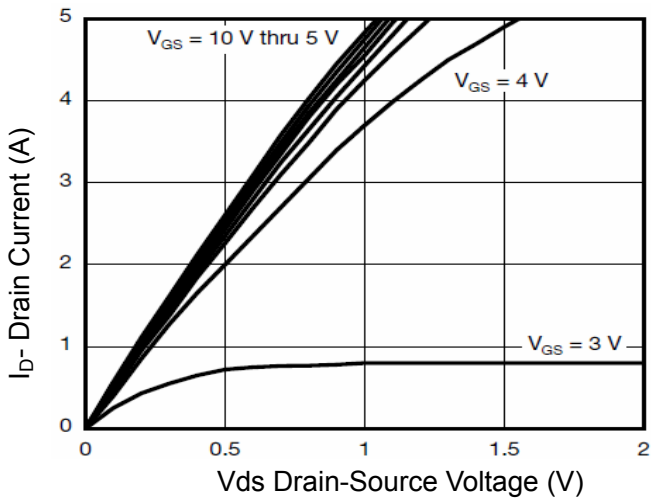
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	3	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A, T <sub>J</sub> =25°C	---	---	1.2	V

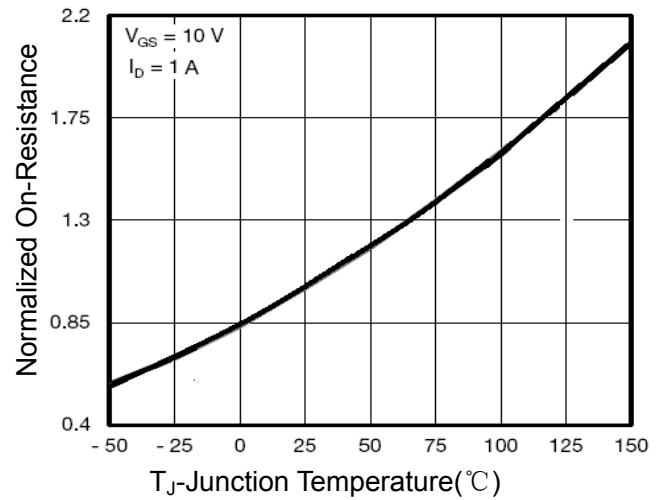
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

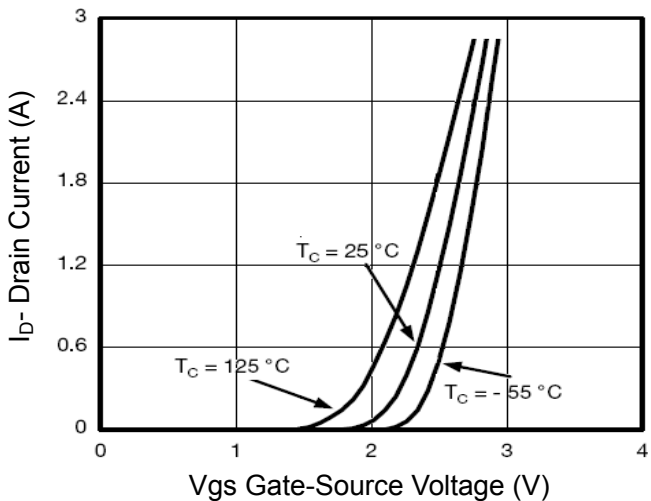
**Typical Characteristics**



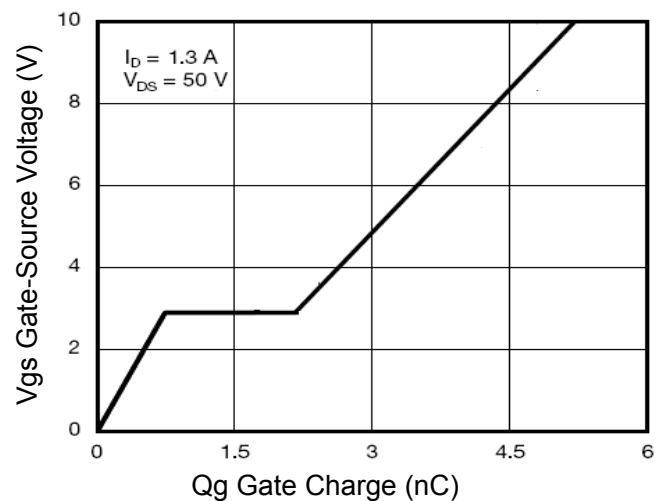
**Figure 1 Output Characteristics**



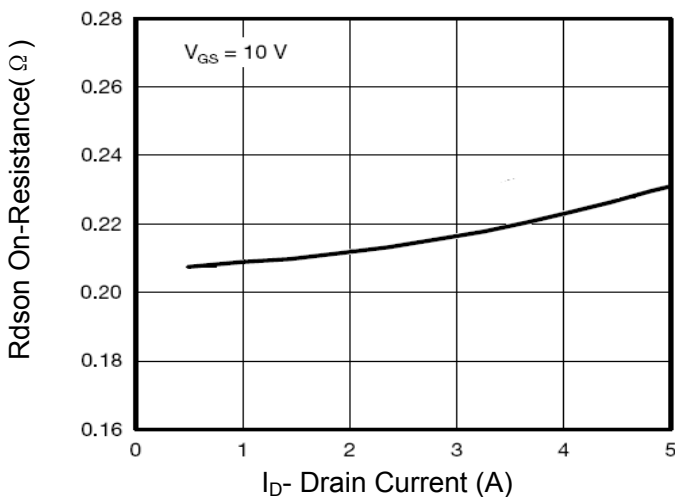
**Figure 4  $R_{dson}$ -Junction Temperature**



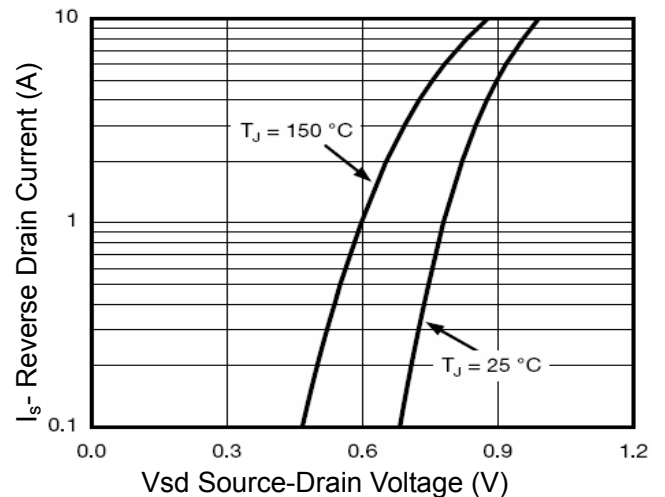
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**

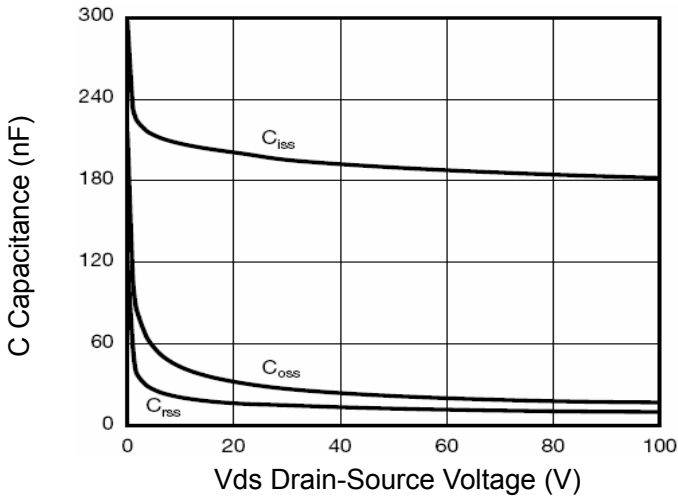


**Figure 3  $R_{dson}$ - Drain Current**

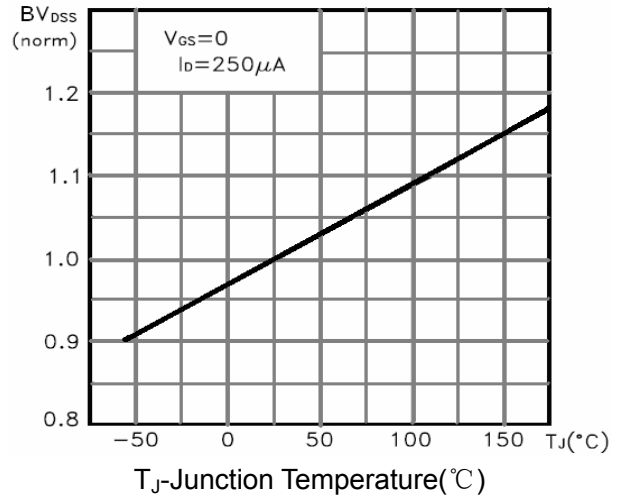


**Figure 6 Source- Drain Diode Forward**

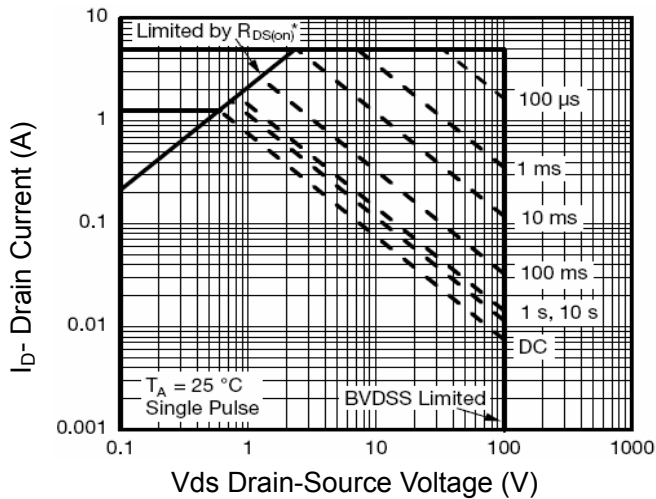
**Typical Characteristics**



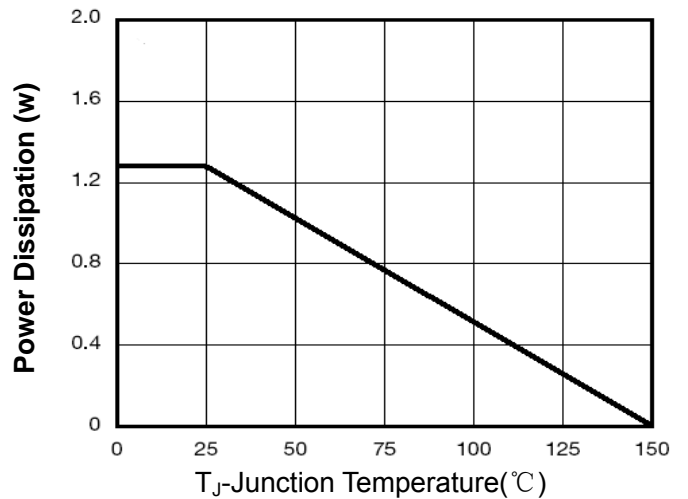
**Figure 7 Capacitance vs Vds**



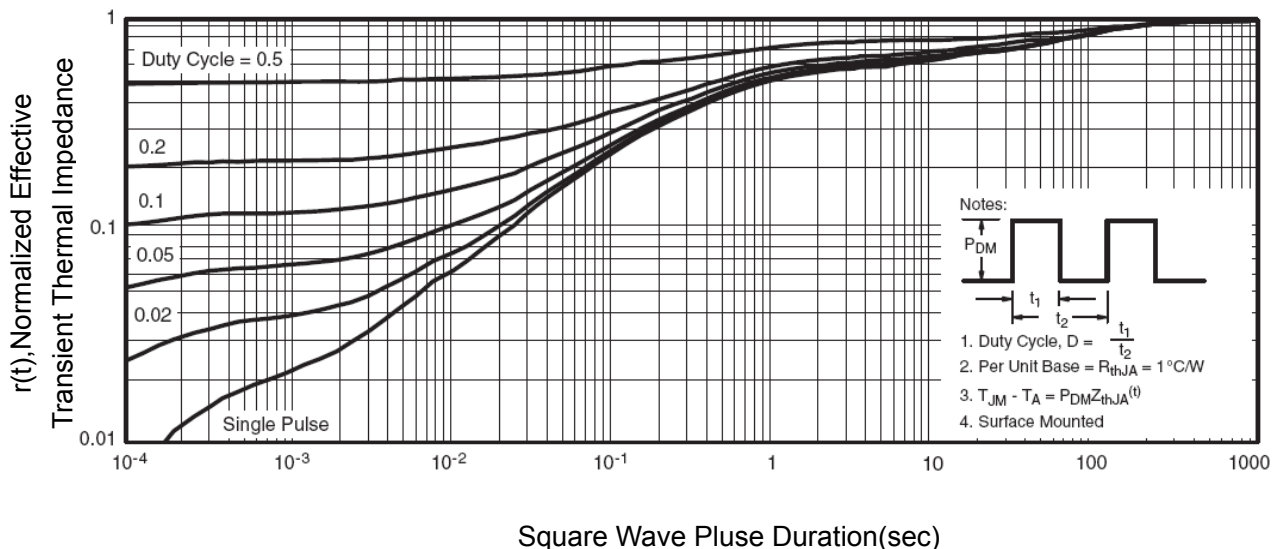
**Figure 9 BV<sub>DSS</sub> vs Junction Temperature**



**Figure 8 Safe Operation Area**



**Figure 10 Power De-ratin**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



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